
2SK1313(L)(S), 2SK1314(L)(S)

Silicon N-Channel MOS FET

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Application

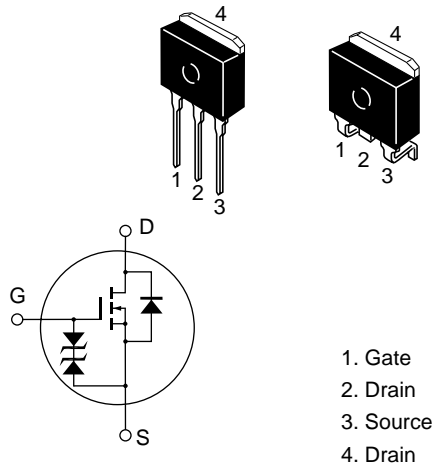
High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator and DC-DC converter

Outline

LDDPAK



2SK1313(L)(S), 2SK1314(L)(S)

Absolute Maximum Ratings (T_a = 25°C)

Item		Symbol	Ratings	Unit
Drain to source voltage	2SK1313	V _{DSS}	450	V
	2SK1314		500	
Gate to source voltage		V _{GSS}	±30	V
Drain current		I _D	5	A
Drain peak current		I _{D(pulse)} ^{*1}	20	A
Body to drain diode reverse drain current		I _{DR}	5	A
Channel dissipation		P _{ch} ^{*2}	50	W
Channel temperature		T _{ch}	150	°C
Storage temperature		T _{stg}	-55 to +150	°C

Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%

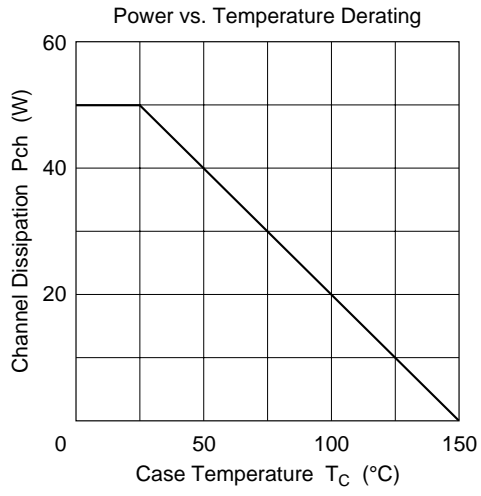
2. Value at T_c = 25°C

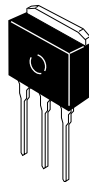
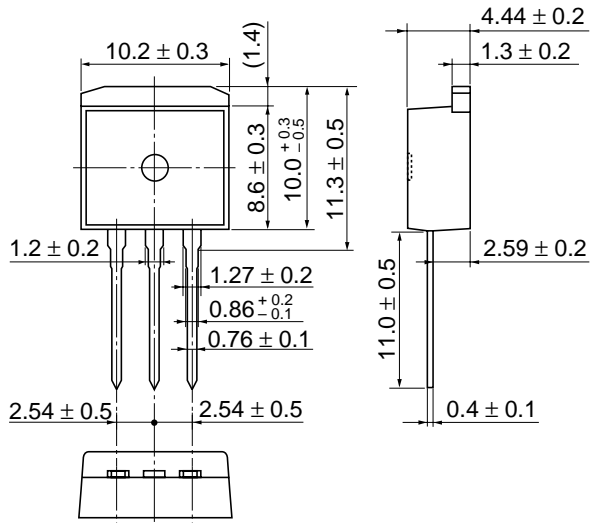
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	2SK1313 $V_{(BR)DSS}$ 2SK1314	450 500	—	—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	± 30	—	—	V	$I_G = \pm 100 \mu\text{A}, V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	2SK1313 I_{DSS} 2SK1314	—	—	250	μA	$V_{DS} = 360 \text{ V}, V_{GS} = 0$ $V_{DS} = 400 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	2.0	—	3.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static Drain to source on state resistance	2SK1313 $R_{DS(on)}$ 2SK1314	— —	1.0 1.2	1.4 1.5	Ω	$I_D = 2.5 \text{ A}, V_{GS} = 10 \text{ V}^{*1}$
Forward transfer admittance	$ y_{fs} $	2.5	4.0	—	S	$I_D = 2.5 \text{ A}, V_{DS} = 10 \text{ V}^{*1}$
Input capacitance	C_{iss}	—	640	—	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$
Output capacitance	C_{oss}	—	160	—	pF	$f = 1 \text{ MHz}$
Reverse transfer capacitance	C_{rss}	—	20	—	pF	
Turn-on delay time	$t_{d(on)}$	—	10	—	ns	$I_D = 2.5 \text{ A}, V_{GS} = 10 \text{ V},$
Rise time	t_r	—	25	—	ns	$R_L = 12 \Omega$
Turn-off delay time	$t_{d(off)}$	—	50	—	ns	
Fall time	t_f	—	30	—	ns	
Body to drain diode forward voltage	V_{DF}	—	0.95	—	V	$I_F = 5 \text{ A}, V_{GS} = 0$
Body to drain diode reverse recovery time	t_{rr}	—	300	—	ns	$I_F = 5 \text{ A}, V_{GS} = 0,$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

Note: 1. Pulse test

See characteristic curves of 2SK1155, 2SK1156.





Hitachi Code	LPAK (L)
JEDEC	—
EIAJ	—
Weight (reference value)	1.4 g

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